

Predicting Vibrational Mean Free Paths in Disordered Systems

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Abstract

I. INTRODUCTION

Measurements by Moon. Measurements by all the refs from Galli paper. The key to understanding such measurement is to estimate a MFP for the vibrational modes in disordered systems. Ref Cahill paper, $v_g = v_s$. Ref Galli paper, its unclear what the group velocity should be.

The goal of this work is to predict the MFP of vibrational modes in disordered systems. Simple Lennard-Jones systems will be studied. LJ crystals are alloyed with a species of differing mass and amorphous samples are prepared. The vibrational modes in these disordered systems are characterized as propagating (phonon) and non-propagating (diffuson) modes by predicting the mode lifetimes and mean free paths. Estimating an effective dispersion relation is required for calculating group velocities for disordered modes, which is crucial for transforming lifetimes to MFPs. The spectrum of phonon MFPs and the accumulated thermal conductivity are predicted for a model of amorphous silicon. Predictions of thermal conductivity using a boundary scattering model demonstrates

II. DETERMINING PROPAGATING AND LOCALIZED MODES

Klemens scattering paper showing rayleigh[?].

Duda shows the reduction in group velocity of disordered systems.[?]

Garg show that the virtual crystal approximation works well for Si-Ge[?]

Duda shows that taking a perfect alloy and disordering via an order parameter allows control of thermal conductivity.[?]

Tamura gives an expression for mass defect scattering which is harmonic and given by[?] : The Rayleigh scattering limit is observed in the low-frequency limit, where the DOS is approximately Debye.

Cahill shows that conductivity of Ge-doped Si epitaxial layers agrees with the defect scaling cross section is captured mostly by the mass disorder.[?]

Cahill shows that even though the mass difference between Si and Ge is larger than the mass of Si, the defect scaling agrees with experimental measurements of thermal conductivity in dilute SiGe epitaxial layers.[?]

Tian showed, using ab initio calculations, that the virtual crystal approximation with

defect scalings work well for predicting the thermal conductivity of PbSe/PbTe alloys.[?]

Bouchard show that alloy DOS varies smoothly with concentration.[?]

III. THERMAL CONDUCTIVITY REDUCTION MECHANISMS

A. Lifetimes

- compare these predicted lifetimes to predictions from:

$$\frac{1}{\tau_d} = \frac{\pi}{2N} \omega^2(\boldsymbol{\kappa}) \sum_{\boldsymbol{\kappa}', \nu'}^{N, 3n} \delta(\omega(\boldsymbol{\kappa}) - \omega(\boldsymbol{\kappa}')) \sum_b^n g(b) |e^*(\boldsymbol{\kappa} \ b) \dot{e}(\boldsymbol{\kappa}' \ b)|^2, \quad (1)$$

B. Mass Disorder

why not bond disorder? This has been investigated such as in Schelling Si/Ge[?], where it was shown that mass disorder is the dominant scattering mechanism.

Marzari Si/Ge PRL[?]. Although, detailed study of PbTe/PbSe systems demonstrate the importance of bond environment for alloys.[?]

C. Group Velocity

- $v_g(m_r)$
- two masses with $v_g(m_r)$, maybe compare with 4 masses with higher mass ratio.
- Keep m_{avg} constant for all.
- run a system with a "softer" and "stiffer" LJ (smaller/bigger eps or sigma). This can be used as a comparison for the phonon/diffuson spectrums which will be shown later.

D. Phonon Lifetimes

- compare lifetimes from 2 atom alloy, 4 atom alloy. Is the reduction in thermal conductivity mostly due to the reduction in group velocities/introduction of optical modes?

IV. DISORDERED ALLOYS

A. Effective Phonon Dispersion

- compare versus virtual crystal

B. Effective Phonon Lifetimes

- compare $c=0.0, 0.05, 0.15$

$$g(b) = \sum_i f_i(b) [1 - m_i(b)/m_{avg}(b)]^2$$

C. Disappearance of SED Peaks

- show SED plot of mode peaks from $c=0.0, 0.05, 0.15, 0.5$ for any mode where a peak still shows in 0.5

D. Propagating Modes in Heavily Disordered Alloys

- Analysis of $c=0.5$ modes at γ , which modes are plane-wave like?

V. HEAT TRANSPORT IN AMORPHOUS SYSTEM

A. Effective Phonon Dispersion

- compare predicted sound speeds from finite dispersion acoustic branch ($dk \pi/100L$), bulk modulus

B. Allen Feldman Diffuson Theory

- thermal transport in terms of a diffusivity, no need for a propagation velocity

C. Diffuson Lifetimes

- measured using NMD and anharmonic MD.

- extract effective Diffuson velocity, compare to sound speed
- use sound speed to predict a phonon MFP, establish a MFP cut-off criteria to call something a phonon or not. Could be MFP \lesssim lattice constant or something. However, there are no wavelengths (yet).

D. Propagating Modes in Amorphous System

- Analysis of $c=0.5$ modes at gamma, which modes are plane-wave like? This will be the key to the length scale needed to compare with the MFP predicted above. The plane-wave like modes will be identified by fourier transforming the eigvec. It should show content at a small number of wavevectors, and 1 should be dominant and of the order of π/L .

E. Role of Anharmonicity in Disordered Thermal Transport

- run harmonic FC MD, predict thermal conductivity using GK
- compare anharmonic GK, harmonic GK, and AF predictions. May possibly need to run "stiffer" system to compare with $k_{si} = k_{ph} + k_{AF} = 0.5 + 0.5$.

VI. THERMAL DIFFUSIVITY IN ORDERED AND DISORDERED SYSTEMS

- plot AF and phonon diffusivities for all systems above.
- Show that for high mass ratio ordered alloys and disordered alloys, the thermal diffusivities are on the order of amorphous system.
- For high mass ratio ordered alloys, it is the reduction of the group velocities through decreased acoustic and introduced optical branches.
- For the disordered alloys, the phonon lifetimes of high frequency modes are drastically reduced as alloy concentration is increased. Should show that this effect is less drastic for "soft" (soft bond) or "acoustically" matched systems (low mass ratio). It is more drastic for large acoustically mismatched systems (high mass ratio) or stiff systems.
- For amorphous systems, there is not a unique choice of the phonon MFP. Instead, it is helpful to consider the diffusons and their thermal diffusivity. Compared to high mass ratio ordered alloys and heavily disordered alloys, these thermal diffusivities are comparable.

- Compare high mass ratio ordered alloys optical branch group velocities/lifetimes (diffusivities) to amorphous diffusivities ("group velocity" and "lifetime"). Are they really distinguishable?

Appendix A: Predicting Phonon Properties

1. Vibrations in Ordered and Disordered Solids

In a crystal (periodic) system, the vibrations of atoms are described by a basis of eigenfunctions called phonon normal modes, which are determined by the properties of the crystal (see Appendix A 3). The eigenvalues of this basis are the phonon mode frequencies (energies).[?] The atomic velocities can be represented by the velocity normal mode coordinate, defined as[?]

$$\dot{u}_\alpha(l; t) = \sum_{\kappa', \nu}^{N, 3n} \frac{1}{\sqrt{m_b N}} \exp[i\kappa' \cdot \mathbf{r}_0(l)] e^*(\kappa'_{\nu} \text{ }^b_{\alpha}) \dot{q}(\kappa'; t). \quad (\text{A1})$$

Here, $\dot{q}(\kappa'; t)$ represents the kinetic energy $T(\kappa'; t)$ of the mode with phonon frequency $\omega_0(\kappa'_{\nu})$ by[?]

$$T(\kappa'; t) = \frac{\dot{q}^*(\kappa'; t) \dot{q}(\kappa'; t)}{2}. \quad (\text{A2})$$

The phonon mode kinetic energies $T(\kappa'; t)$ are used to calculate the phonon spectral energy density in Appendix A 2.

2. Predicting Phonon Lifetimes using Spectral Energy Density

The phonon normal mode coordinate is,

$$\dot{q}(\kappa'; t) = \sum_{\alpha, b, l}^{3, n, N} \sqrt{\frac{m_b}{N}} \dot{u}_\alpha(l; t) e^*(\kappa'_{\nu} \text{ }^b_{\alpha}) \exp[i\kappa' \cdot \mathbf{r}_0(l)], \quad (\text{A3})$$

which form the basis for vibrations in ordered materials and represents the phonon mode kinetic energy. The normal mode kinetic energy can be transformed from the time domain t to the frequency domain ω by Parseval's theorem,[?]

$$T(\kappa'; \omega) = \lim_{\tau_0 \rightarrow \infty} \frac{1}{2\tau_0} \left| \frac{1}{\sqrt{2\pi}} \int_0^{\tau_0} \dot{q}(\kappa'; t) \exp(-i\omega t) dt \right|^2. \quad (\text{A4})$$

FIG. 1: The SED (Φ) for the first three polarizations at the wavevector $[\pi/4a, \pi/4a, \pi/4a]$ for LJ argon at a temperature of 20 K. There are two degenerate transverse acoustic polarizations and one longitudinal acoustic polarization (of higher frequency).[?] When fitting the SED, the different polarizations can be fit individually using single Lorentzian peaks or as a superposition of peaks. Here the two peaks are fit individually with Φ plotted as a superposition. The predicted lifetimes of these polarizations, which are inversely proportional to the peak widths Γ , are provided in the legend.

Here, $T(\boldsymbol{\kappa}; \omega)$ represents the spectral energy of the phonon normal mode with frequency $\omega(\boldsymbol{\kappa}; \omega)$. Following the derivation in Appendix ??, one arrives at the expression for the SED of a single phonon mode,

$$T(\boldsymbol{\kappa}; \omega) = \frac{C_0(\boldsymbol{\kappa})}{2} \frac{\Gamma(\boldsymbol{\kappa})/\pi}{[\omega_0(\boldsymbol{\kappa}) - \omega]^2 + \Gamma^2(\boldsymbol{\kappa})}, \quad (\text{A5})$$

which is a Lorentzian function with center at $\omega_0(\boldsymbol{\kappa})$ and a half-width at half-maximum (linewidth) of $\Gamma(\boldsymbol{\kappa})$ and $C_0(\boldsymbol{\kappa})$ is a constant. We know from anharmonic lattice dynamics theory that the phonon linewidth is related to the phonon lifetime, $\tau(\boldsymbol{\kappa})$, by[?] ?

$$\tau(\boldsymbol{\kappa}) = \frac{1}{2\Gamma(\boldsymbol{\kappa})}. \quad (\text{A6})$$

The MD simulations we perform here are classical. For a classical system in the harmonic limit (i.e., temperature approaching zero) there is an equipartition of energy and $\sum_{\nu}^{3n} T(\boldsymbol{\kappa}; \omega) = \sum_{\nu}^{3n} V(\boldsymbol{\kappa}; \omega)$.[?] In an anharmonic system (i.e., a MD simulation), the assumption of equipartition of energy can be tested by predicting the system-level specific heat. By assuming equipartition of energy, the phonon SED at a particular wavevector is

$$\Phi(\boldsymbol{\kappa}, \omega) = 2 \sum_{\nu}^{3n} T(\boldsymbol{\kappa}; \omega) = \sum_{\nu}^{3n} C_0(\boldsymbol{\kappa}) \frac{\Gamma(\boldsymbol{\kappa})/\pi}{[\omega_0(\boldsymbol{\kappa}) - \omega]^2 + \Gamma^2(\boldsymbol{\kappa})}, \quad (\text{A7})$$

which is a superposition of $3n$ Lorentzian functions with centers at $\omega_0(\boldsymbol{\kappa})$ (one for each polarization). For simplicity, we refer to $\Phi(\boldsymbol{\kappa}, \omega)$ as Φ . Given a set of atomic velocities, Φ can be calculated using Eq. (??) and (??), and then fit using Eq. (??) to extract the phonon properties $\omega_0(\boldsymbol{\kappa})$ and $\tau(\boldsymbol{\kappa})$.

3. Allowed Wavevectors in Ordered Systems

The phonon spectral energy is defined for the allowed wavevectors of a crystal, which can be specified from the crystal structure's Bravais lattice and its basis, i.e. unit cell. A D -dimensional Bravais lattice is a collection of points with positions

$$\mathbf{u}_0(l) = \sum_{\alpha}^D N_{\alpha} \mathbf{a}_{\alpha} \quad (\text{A8})$$

where N_{α} and the summations if over the lattice vectors, \mathbf{a}_{α} .[?] The basis (or unit cell) is the building block of the crystal and they are arranged on the points defined by the Bravais lattice. The equilibrium position of any atom in the crystal can be described by

$$\mathbf{u}_0(l) = \mathbf{u}_0(l) + \mathbf{u}_0(b) \quad (\text{A9})$$

where $\mathbf{u}_0(l)$ is the equilibrium position of the l^{th} unit cell and $\mathbf{u}_0(b)$ is the equilibrium position of the b^{th} atom in the unit cell relative to $\mathbf{u}_0(l)$. For the LJ systems studied here, the cubic conventional cells are used with four atoms per unit cell.[?] For our MD simulations, cubic simulation domains with periodic boundary conditions are used with $N_1 = N_2 = N_3 = N_0$.[?] The allowed wavevectors for such crystal structures are

$$\boldsymbol{\kappa} = \sum_{\alpha} \mathbf{b}_{\alpha} \frac{n_{\alpha}}{N_{\alpha}}, \quad (\text{A10})$$

where \mathbf{b}_{α} are the reciprocal lattice vectors[?] and $-N_{\alpha}/2 < n_{\alpha} \leq N_{\alpha}/2$, where n_{α} are integers and N_{α} are even integers.[?] The wavevectors are taken to be in the first Brillouin zone.[?]

Allowed Wavevectors in Disordered Materials

Strictly speaking, the only allowed wavevector in a disordered system is the gamma point ($\kappa = [000]$). As such, the lattice dynamics calculations are performed at the gamma point:

4. Thermal Conductivity

Once the lifetimes (MFPs) and group velocities of all vibrational modes in the Brillouin zone are obtained, the bulk thermal conductivity in direction \mathbf{n} , $k_{\mathbf{n}}$, can be calculated from[?]

$$k_{\mathbf{n}} = \sum_{\boldsymbol{\kappa}} \sum_{\nu} c_{ph}(\boldsymbol{\kappa}) v_{g,\mathbf{n}}^2(\boldsymbol{\kappa}) \tau(\boldsymbol{\kappa}). \quad (\text{A11})$$

Here, c_{ph} is the phonon volumetric specific heat and $v_{g,\mathbf{n}}$ is the component of the group velocity vector in direction \mathbf{n} . Since the systems we consider are classical and obey Maxwell-Boltzmann statistics,[?] the specific heat is k_B/V per mode in the harmonic limit where V is the system volume. This approximation is used here and has been shown to be suitable for LJ argon[?] and SW silicon.[?] The group velocity vector is the gradient of the dispersion curves (i.e., $\partial\omega/\partial\boldsymbol{\kappa}$), which can be calculated from the frequencies and wavevectors using finite differences. In this work, the group velocities are calculated using finite difference and quasi-harmonic lattice dynamics because a very small finite difference can be used which reduces the error.[?] To predict a bulk thermal conductivity, it is necessary to perform a finite simulation size scaling procedure as discussed in Appendix B.

Appendix B: Finite Simulation-Size Scaling for Thermal Conductivity

For the LJ argon system studied in Section ??, a finite simulation-size scaling procedure[?] is used to compare the thermal conductivity predictions from Φ and Φ' to those from the Green-Kubo method. The scaling procedure is demonstrated in Fig. 2. The thermal conductivity is predicted from Φ or Φ' and MD simulations with $N_0 = 4, 6, 8$, and 10. The bulk conductivity, k_∞ , is then estimated by fitting the data to

$$1/k = 1/k_\infty + A/N_0, \tag{B1}$$

where A is a constant. This procedure is necessary because the first Brillouin zone is only sampled at a finite number of points for a finite simulation size, with no contribution from the volume at its center. To predict a bulk thermal conductivity, it is important to sample points near the Brillouin zone center, where the modes can have large lifetimes and group velocities.[?]

FIG. 2: Thermal conductivity predictions for LJ argon calculated using phonon lifetimes predicted by Φ and Φ' .[?] (a) The finite simulation-size scaling extrapolation[?] [?] is used to compare the results to bulk predictions made using the Green-Kubo method. (b) The bulk results for Φ and Green-Kubo are in good agreement temperatures of 20 and 40 K with those of other atomistic simulation methods.[?]

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